

# MOSFET – Power, Single, N-Channel

## 100 V, 4.8 mΩ, 132 A

## NTMFS6B03N

### Features

- Small Footprint (5x6 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter                                                           | Symbol         | Value                                          | Unit             |
|---------------------------------------------------------------------|----------------|------------------------------------------------|------------------|
| Drain-to-Source Voltage                                             | $V_{DS}$       | 100                                            | V                |
| Gate-to-Source Voltage                                              | $V_{GS}$       | $\pm 20$                                       | V                |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3)            | $I_D$          | $T_C = 25^\circ\text{C}$                       | 132 A            |
|                                                                     |                | $T_C = 100^\circ\text{C}$                      |                  |
| Power Dissipation $R_{\theta JC}$ (Notes 1, 2)                      | $P_D$          | $T_C = 25^\circ\text{C}$                       | 165 W            |
|                                                                     |                | $T_C = 100^\circ\text{C}$                      |                  |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)            | $I_D$          | $T_A = 25^\circ\text{C}$                       | 19 A             |
|                                                                     |                | $T_A = 100^\circ\text{C}$                      |                  |
| Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)                     | $P_D$          | $T_A = 25^\circ\text{C}$                       | 3.4 W            |
|                                                                     |                | $T_A = 100^\circ\text{C}$                      |                  |
| Pulsed Drain Current                                                | $I_{DM}$       | $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | 470 A            |
| Operating Junction and Storage Temperature                          | $T_J, T_{stg}$ | $-55$ to $+150$                                | $^\circ\text{C}$ |
| Source Current (Body Diode)                                         | $I_S$          | 160                                            | A                |
| Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 60$ A) | $E_{AS}$       | 180                                            | mJ               |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s)   | $T_L$          | 260                                            | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter                                   | Symbol          | Value | Unit                      |
|---------------------------------------------|-----------------|-------|---------------------------|
| Junction-to-Case – Steady State             | $R_{\theta JC}$ | 0.76  | $^\circ\text{C}/\text{W}$ |
| Junction-to-Ambient – Steady State (Note 2) | $R_{\theta JA}$ | 38    |                           |

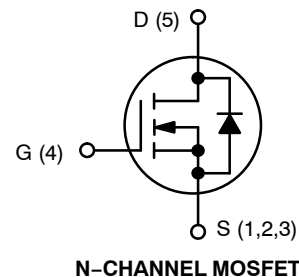
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



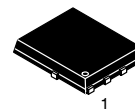
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

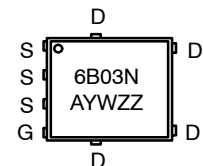
| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 100 V         | 4.8 mΩ @ 10 V            | 132 A             |



### MARKING DIAGRAM



DFN5 (SO-8FL)  
CASE 506EZ



A = Assembly Location  
Y = Year  
W = Work Week  
ZZ = Lot Traceability

### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

# NTMFS6B03N

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                           |                   |                                                     |                                  |      |     |                      |
|-----------------------------------------------------------|-------------------|-----------------------------------------------------|----------------------------------|------|-----|----------------------|
| Drain-to-Source Breakdown Voltage                         | $V_{(BR)DSS}$     | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 100                              |      |     | V                    |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ |                                                     |                                  | 67.3 |     | mV/ $^\circ\text{C}$ |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$         | $V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$         | $T_J = 25\text{ }^\circ\text{C}$ |      | 10  | $\mu\text{A}$        |
|                                                           |                   |                                                     | $T_J = 125^\circ\text{C}$        |      | 100 |                      |
| Gate-to-Source Leakage Current                            | $I_{GSS}$         | $V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$         |                                  |      | 100 | nA                   |

### ON CHARACTERISTICS (Note 4)

|                                   |                  |                                                 |     |      |     |                      |
|-----------------------------------|------------------|-------------------------------------------------|-----|------|-----|----------------------|
| Gate Threshold Voltage            | $V_{GS(TH)}$     | $V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$ | 2.0 |      | 4.0 | V                    |
| Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ |                                                 |     | -8.1 |     | mV/ $^\circ\text{C}$ |
| Drain-to-Source On Resistance     | $R_{DS(on)}$     | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}$       |     | 3.8  | 4.8 | m $\Omega$           |
|                                   |                  | $V_{GS} = 6.0\text{ V}, I_D = 10\text{ A}$      |     | 6.0  | 7.8 |                      |

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                              |              |                                                                 |  |      |  |          |
|------------------------------|--------------|-----------------------------------------------------------------|--|------|--|----------|
| Input Capacitance            | $C_{ISS}$    | $V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 50\text{ V}$   |  | 4200 |  | pF       |
| Output Capacitance           | $C_{OSS}$    |                                                                 |  | 760  |  |          |
| Reverse Transfer Capacitance | $C_{RSS}$    |                                                                 |  | 31   |  |          |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}; I_D = 50\text{ A}$ |  | 58   |  | nC       |
| Threshold Gate Charge        | $Q_{G(TH)}$  |                                                                 |  | 6.2  |  |          |
| Gate-to-Source Charge        | $Q_{GS}$     |                                                                 |  | 19   |  |          |
| Gate-to-Drain Charge         | $Q_{GD}$     |                                                                 |  | 17   |  |          |
| Plateau Voltage              | $V_{GP}$     |                                                                 |  | 5.4  |  | V        |
| Gate Resistance              | $R_G$        | $T_J = 25\text{ }^\circ\text{C}$                                |  | 1.0  |  | $\Omega$ |

### SWITCHING CHARACTERISTICS (Note 5)

|                     |              |                                                                                          |  |    |  |    |
|---------------------|--------------|------------------------------------------------------------------------------------------|--|----|--|----|
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}, I_D = 50\text{ A}, R_G = 1.0\text{ }\Omega$ |  | 16 |  | ns |
| Rise Time           | $t_r$        |                                                                                          |  | 46 |  |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |                                                                                          |  | 29 |  |    |
| Fall Time           | $t_f$        |                                                                                          |  | 11 |  |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |          |                                                                              |                           |     |     |     |   |
|-------------------------|----------|------------------------------------------------------------------------------|---------------------------|-----|-----|-----|---|
| Forward Diode Voltage   | $V_{SD}$ | $V_{GS} = 0\text{ V}, I_S = 50\text{ A}$                                     | $T_J = 25^\circ\text{C}$  |     | 0.9 | 1.2 | V |
|                         |          |                                                                              | $T_J = 125^\circ\text{C}$ |     | 0.8 |     |   |
| Reverse Recovery Time   | $t_{RR}$ | $V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 25\text{ A}$ |                           | 67  |     | ns  |   |
| Charge Time             | $t_a$    |                                                                              |                           | 35  |     |     |   |
| Discharge Time          | $t_b$    |                                                                              |                           | 31  |     |     |   |
| Reverse Recovery Charge | $Q_{RR}$ |                                                                              |                           | 120 |     | nC  |   |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

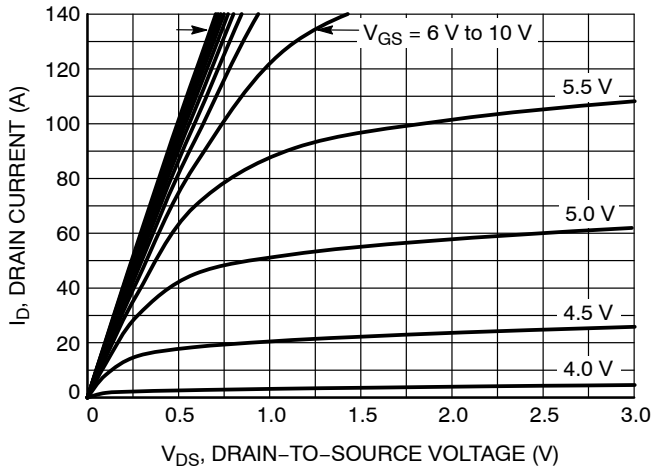


Figure 1. On-Region Characteristics

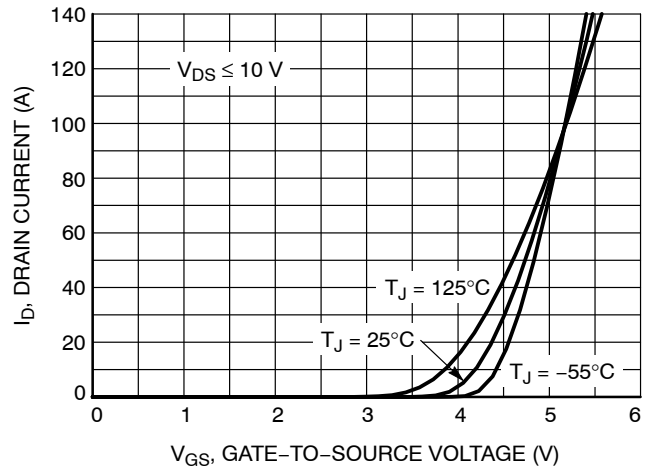


Figure 2. Transfer Characteristics

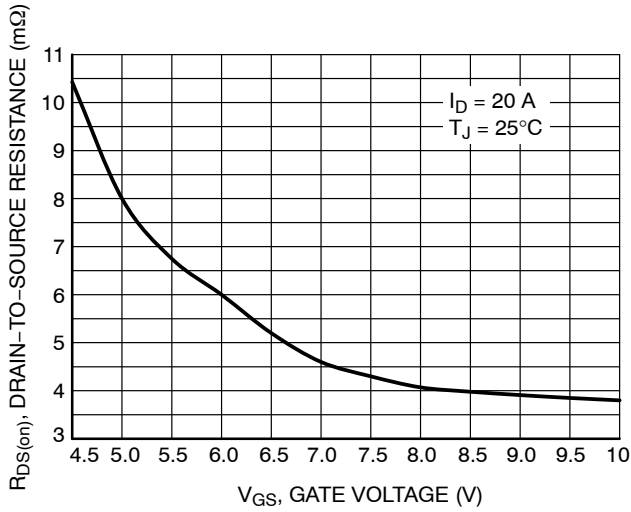


Figure 3. On-Resistance vs. Gate-to-Source Voltage

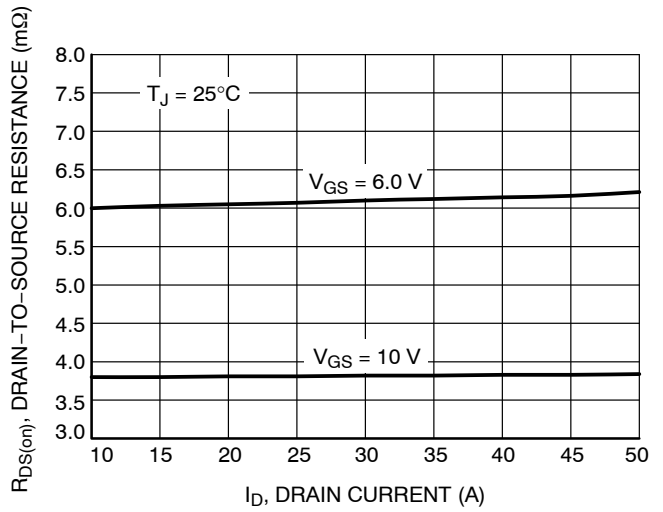


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

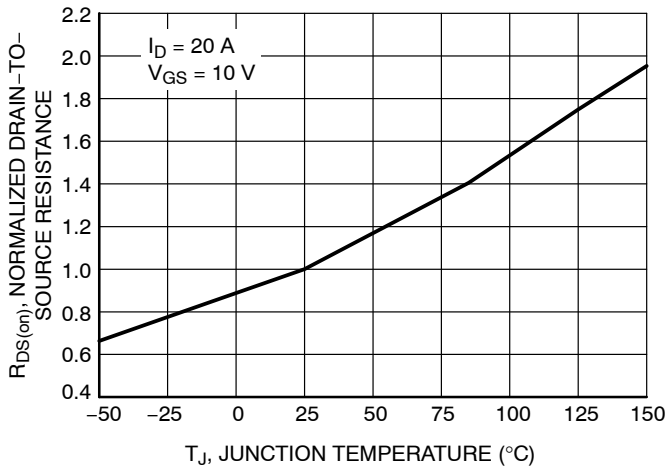


Figure 5. On-Resistance Variation with Temperature

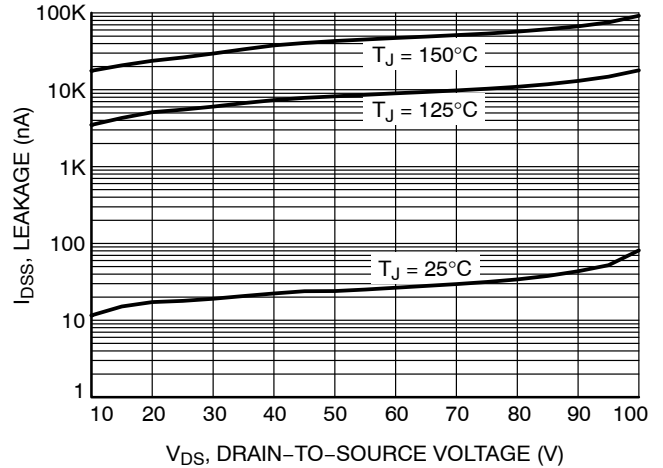
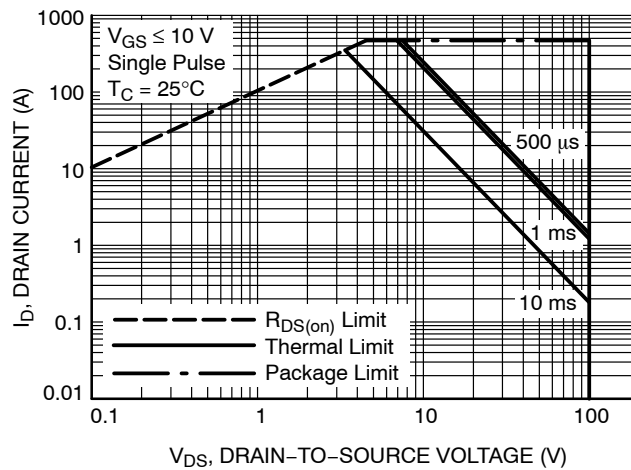
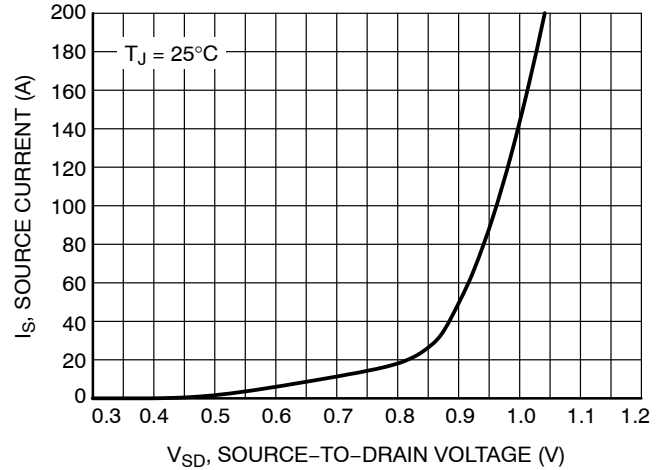
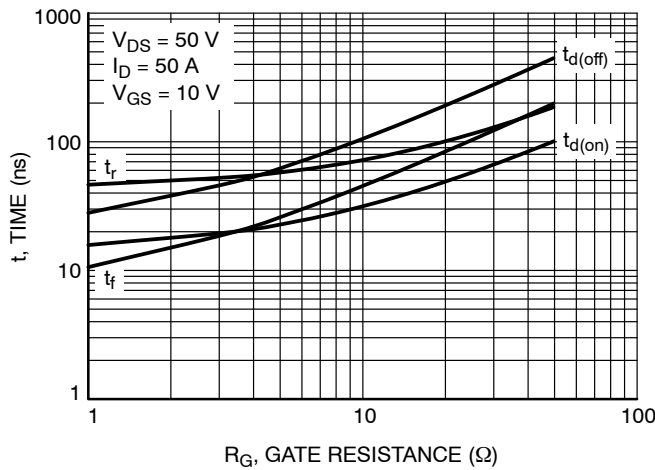
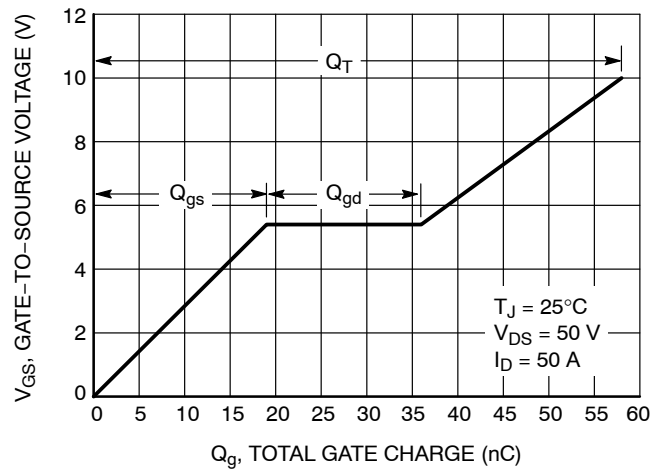
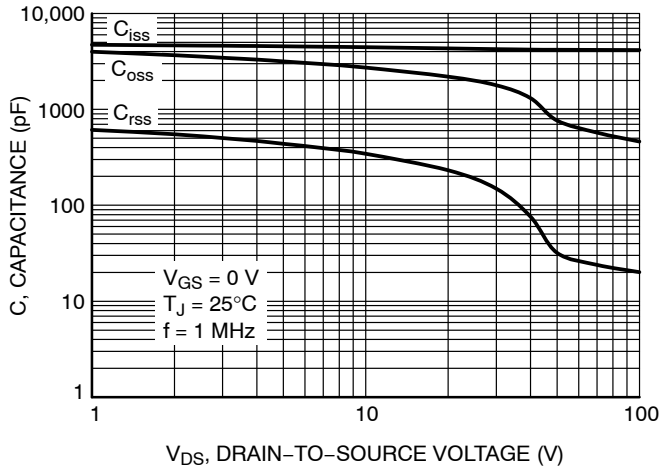


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NTMFS6B03N

## TYPICAL CHARACTERISTICS



# NTMFS6B03N

## TYPICAL CHARACTERISTICS

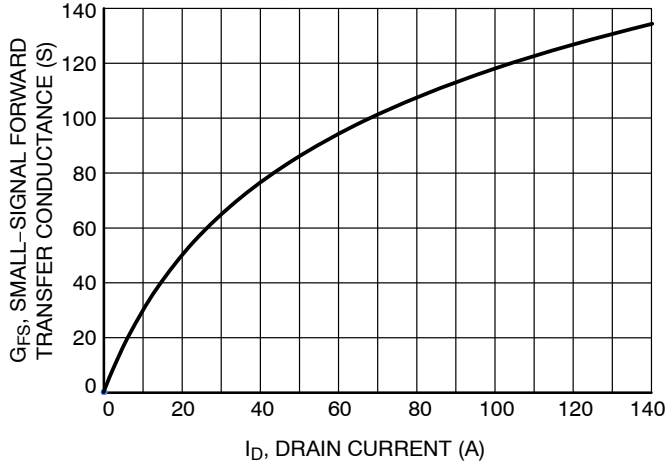


Figure 12.  $G_{FS}$  vs.  $I_D$

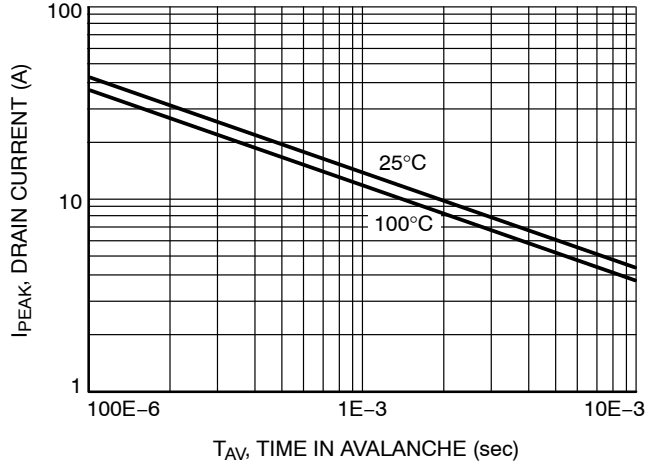


Figure 13.  $I_{PEAK}$  vs.  $T_{AV}$

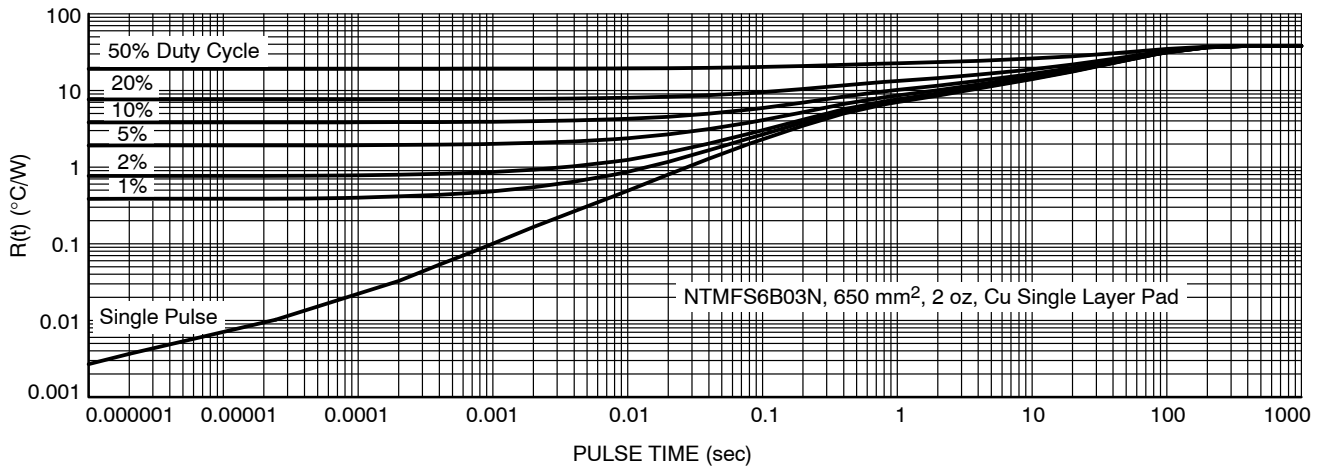


Figure 14. Thermal Response

## DEVICE ORDERING INFORMATION

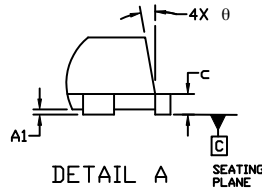
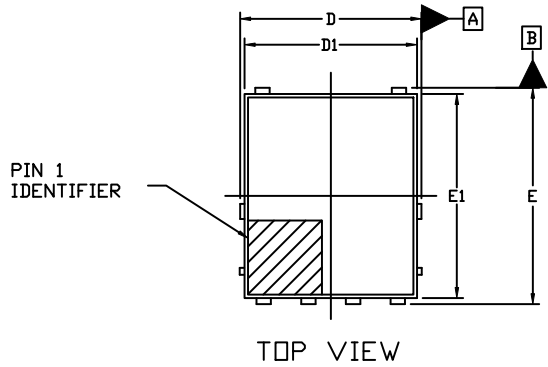
| Device        | Marking | Package           | Shipping†          |
|---------------|---------|-------------------|--------------------|
| NTMFS6B03NT1G | 6B03N   | DFN5<br>(Pb-Free) | 1500 / Tape & Reel |
| NTMFS6B03NT3G | 6B03N   | DFN5<br>(Pb-Free) | 5000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTMFS6B03N

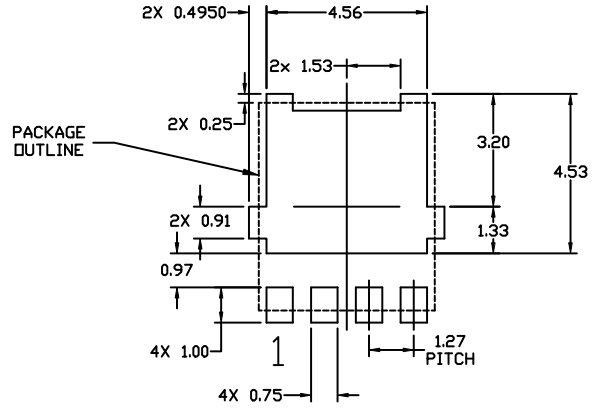
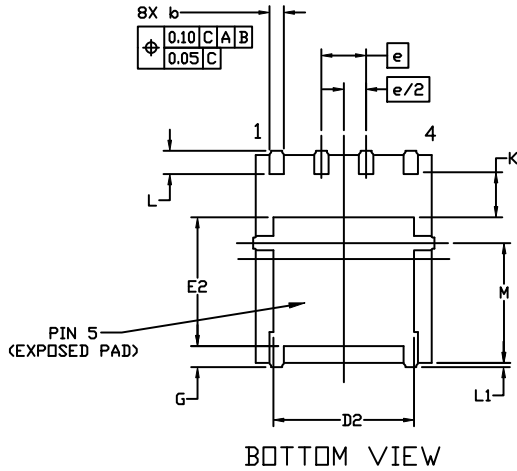
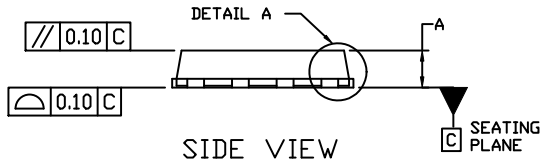
## PACKAGE DIMENSIONS

DFN5 5x6, 1.27P (SO-8FL)  
CASE 506EZ  
ISSUE O



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
  2. CONTROLLING DIMENSION: MILLIMETERS
  3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| MILLIMETERS |          |       |      |
|-------------|----------|-------|------|
| DIM         | MIN.     | NOM.  | MAX. |
| A           | 0.90     | 1.00  | 1.10 |
| A1          | 0.00     | ---   | 0.05 |
| b           | 0.33     | 0.41  | 0.51 |
| c           | 0.23     | 0.28  | 0.33 |
| D           | 5.00     | 5.15  | 5.30 |
| D1          | 4.70     | 4.90  | 5.10 |
| D2          | 3.80     | 4.00  | 4.20 |
| E           | 6.00     | 6.15  | 6.30 |
| E1          | 5.70     | 5.90  | 6.10 |
| E2          | 3.45     | 3.65  | 3.85 |
| e           | 1.27 BSC |       |      |
| G           | 0.51     | 0.575 | 0.71 |
| k           | 1.10     | 1.20  | 1.40 |
| L           | 0.51     | 0.575 | 0.71 |
| L1          | 1.25 REF |       |      |
| M           | 3.00     | 3.40  | 3.80 |
| θ           | 0°       | ---   | 12°  |



- \* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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